

2SC6043 – NPN Epitaxial Planar Silicon Transistors **High-Current Switching Applications**

Applications

· Voltage regulators, relay drivers, lamp drivers, electrical equipment.

Features

- · Adoption of MBIT process.
- High current capacitance.
- · Low collector-to-emitter saturation voltage.
- · High-speed switching.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		80	V
Collector-to-Emitter Voltage	VCES		80	V
Collector-to-Emitter Voltage	VCEO		50	V
Emitter-to-Base Voltage	VEBO		6	V
Collector Current	IC		2	А
Collector Current (Pulse)	ICP		4	А
Base Current	ΙB		400	mA
Collector Dissipation	PC		1	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Sumbol	Conditions		Ratings		
Symbol		min	typ	max	Unit
ICBO	V _{CB} =40V, I _E =0A			1	μΑ
IEBO	VEB=4V, IC=0A			1	μΑ
hFE1	VCE=2V, IC=100mA	200		560	
hFE2	V _{CE} =2V, I _C =1.5A	40			
fT	VCE=10V, IC=300mA		420		MHz
Cob	V _{CB} =10V, f=1MHz		9		pF
	IEBO hFE1 hFE2 fT	ICBO VCB=40V, IE=0A IEBO VEB=4V, IC=0A hFE1 VCE=2V, IC=100mA hFE2 VCE=2V, IC=1.5A fT VCE=10V, IC=300mA	ICBO VCB=40V, IE=0A IEBO VEB=4V, IC=0A hFE1 VCE=2V, IC=100mA hFE2 VCE=2V, IC=1.5A fT VCE=10V, IC=300mA	Symbol Conditions min typ ICBO VCB=40V, IE=0A </td <td>Symbol Conditions min typ max ICBO VCB=40V, IE=0A 1 1 IEBO VEB=4V, IC=0A 1 1 hFE1 VCE=2V, IC=100MA 200 560 hFE2 VCE=2V, IC=1.5A 40 420</td>	Symbol Conditions min typ max ICBO VCB=40V, IE=0A 1 1 IEBO VEB=4V, IC=0A 1 1 hFE1 VCE=2V, IC=100MA 200 560 hFE2 VCE=2V, IC=1.5A 40 420

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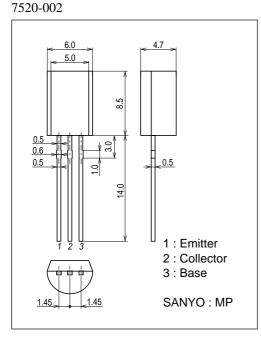
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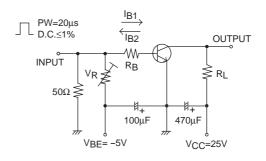
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=1A, IB=50mA		150	300	mV
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	IC=1A, IB=50mA		0.94	1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=10μA, IE=0A	80			V
Collector-to-Emitter Breakdown Voltage	V(BR)CES	IC=100μA, RBE=0Ω	80			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, R _{BE} =∞	50			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	IE=10μA, IC=0A	6			V
Turn-ON Time	ton	See specified Test Circuit.		35		ns
Storage Time	tstg	See specified Test Circuit.		330		ns
Fall Time	tf	See specified Test Circuit.		40		ns

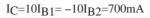
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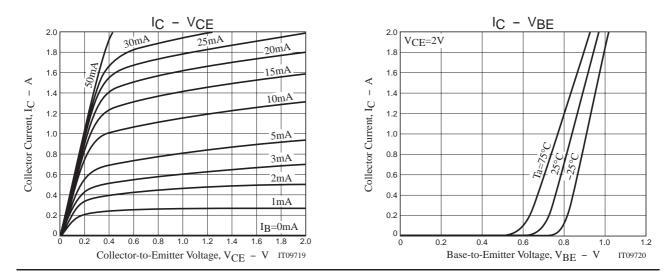
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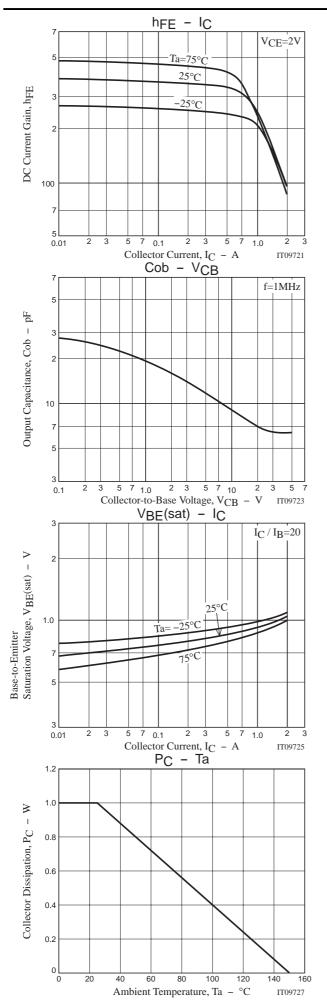


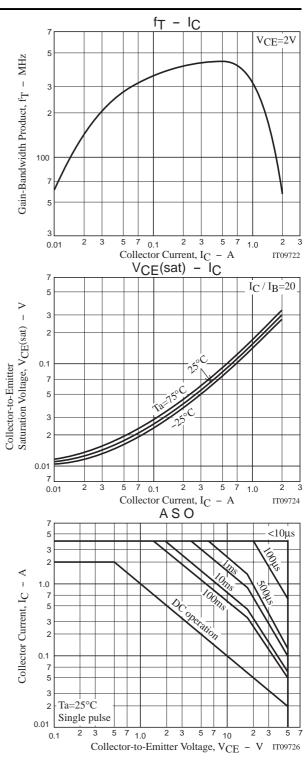
Switching Time Test Circuit











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